

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE40P40L uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

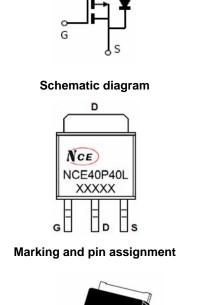
- $V_{DS} = -40V, I_D = -40A$ $R_{DS(ON)} < 14m\Omega @ V_{GS} = -10V$ $R_{DS(ON)} < 24m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



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TO-251S top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40P40L	NCE40P40L	TO-251S	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	-40	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	-28	А
Pulsed Drain Current	I _{DM}	-120	А
Maximum Power Dissipation	PD	80	W
Derating factor		0.53	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	544	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C



Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	1.88	°C/W	1
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Electrical Characteristics (T_c=25[°]C unless otherwise noted)

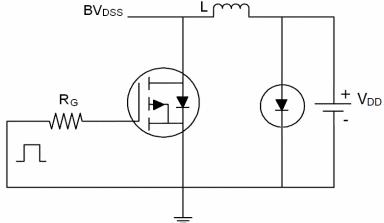
Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-40	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)				•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA	-1.5	-1.9	-3.0	V	
Drain-Source On-State Resistance	P	V _{GS} =-10V, I _D =-12A	-	12	14	mΩ	
	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-12A	-	18.5	24	mΩ	
Forward Transconductance	ransconductance g _{FS} V _{DS} =-5V,I _D =-12A		-	34	-	S	
Dynamic Characteristics (Note4)				•			
Input Capacitance	Clss		-	2960	-	PF	
Output Capacitance	Coss	V _{DS} =-20V,V _{GS} =0V, F=1.0MHz	-	370	-	PF	
Reverse Transfer Capacitance	Crss		-	310	-	PF	
Switching Characteristics (Note 4)	·			•			
Turn-on Delay Time	t _{d(on)}		-	10	-	nS	
Turn-on Rise Time	tr	V _{DD} =-20V,I _D =-20A	-	18	-	nS	
Turn-Off Delay Time	t _{d(off)}	V _{GS} =-10V,R _G =3Ω	-	38	-	nS	
Turn-Off Fall Time	t _f		-	24	-	nS	
Total Gate Charge	Qg	V 001 404	-	42.2	72	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =-20,I _D =-12A, V _{GS} =-10V	-	6.9		nC	
Gate-Drain Charge	Q _{gd}	v _{GS} =-10v	-	9.7		nC	
Drain-Source Diode Characteristics	·			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	-40	Α	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =- 20A	-	40		nS	
Reverse Recovery Charge	Qrr	di/dt = -100A/µs ^(Note3)	-	42		nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

Notes:

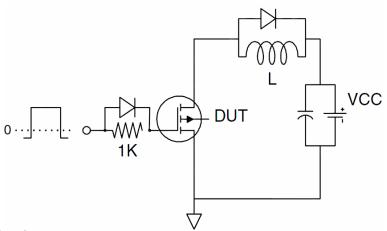
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, t \leq 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=-20V,V_G=-10V,L=1mH,Rg=25\Omega,I_{AS}=33A



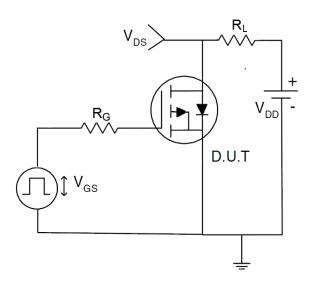
Test Circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

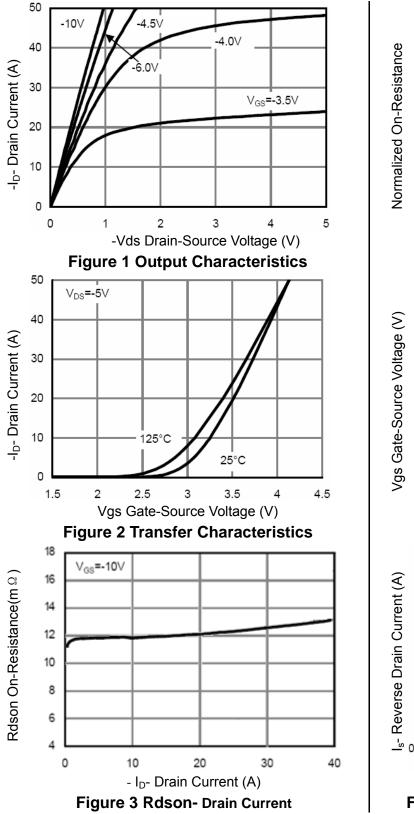


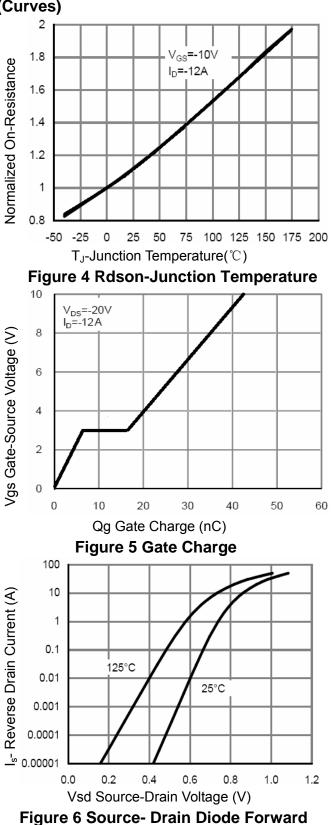
3) Switch Time Test Circuit







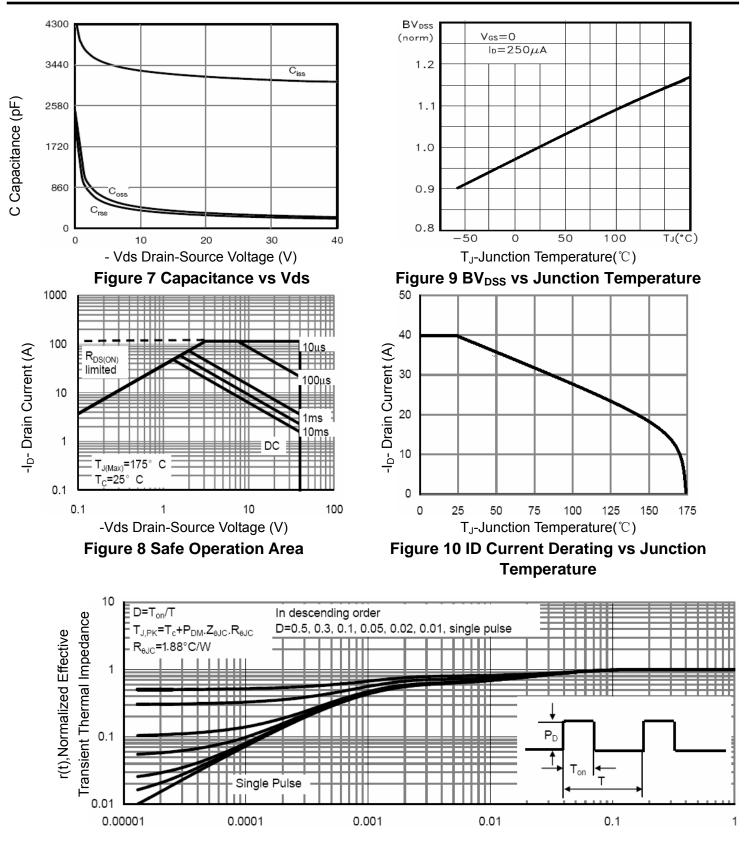






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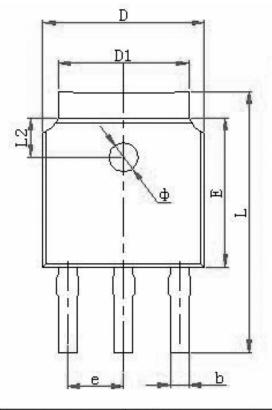
NCE40P40L

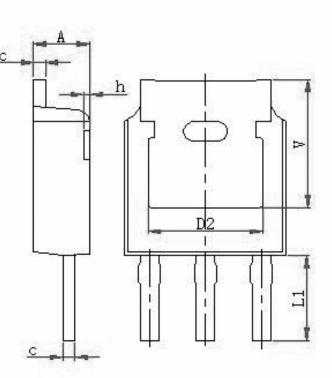


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



TO-251S Package Information





Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
b	0.660	0.860	0.026	0.034	
C	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	10.400	11.000	0.409	0.433	
L1	3.300	3,700	0.130	0.146	
L2	1.600 REF.		0.063	REF.	
Φ	1.100	1.300	0.043	0.051	
h	0.000	0.300	0.000	0.012	
V	5.350 REF.		0.211 REF.		



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